

Product Overview

NGTB15N120L: IGBT 1200V 15A FS1 Gen Mkt

For complete documentation, see the data sheet.



This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop (FS) Trench construction, and provides superior performance in demanding switching applications, offering both low on-state voltage and minimal switching loss. The IGBT is well suited for resonant or soft switching applications. Incorporated into the device is a rugged co-packaged free wheeling diode with a low forward voltage.

Features

- Low Saturation Voltage using Trench with Fieldstop Technology
- Low Switching Loss

Benefits

- Low Conduction Loss
- Reduces system Power Dissipation

Applications

- Industrial Switching

End Products

- Inverter Welding Machines
- Microwave Ovens

For more information please contact your local sales support at www.onsemi.com.

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